

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	1042	((triple near5 well) and (trench open\$3 via hole recess groove)) and (threshold near5 volt\$6)	US-PGPUB; USPAT	OR	ON	2005/01/09 18:58
L2	22360	DHF BOE	US-PGPUB; USPAT	OR	ON	2005/01/09 18:31
L3	16	1 and 2	US-PGPUB; USPAT	OR	ON	2005/01/09 18:35
L4	18597	(insulat\$3 dielectric sacrificial oxide) same (wafer substrate) same (implant\$3 dop\$3) same well	US-PGPUB; USPAT	OR	ON	2005/01/09 19:00
L5	5940	4 and ((inert (heavy atom) Argon Ar Xenon Xe gremanium Ge krypton Kr) same (implant\$3 dop\$3))	US-PGPUB; USPAT	OR	ON	2005/01/09 19:01
L6	5160	5 and ((etch\$3 remov\$3)same (insulat\$3 dielectric sacrificial oxide))	US-PGPUB; USPAT	OR	ON	2005/01/09 19:01
L8	103	6 and ((anti near3 diffusion) ((anti near5 punch near5 through)anti-punchthrough APT))	US-PGPUB; USPAT	OR	ON	2005/01/09 19:02
L9	6	((triple near5 well) and (trench open\$3 via hole recess groove)) and (threshold near5 volt\$4)	USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/09 18:59
L10	4419	(insulat\$3 dielectric sacrificial oxide) and (wafer substrate) and (implant\$3 dop\$3) and well	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/09 19:00
L11	984	10 and ((inert (heavy atom) Argon Ar Xenon Xe gremanium Ge krypton Kr) and (implant\$3 dop\$3))	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/09 19:01
L12	468	11 and ((etch\$3 remov\$3)same (insulat\$3 dielectric sacrificial oxide))	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/09 19:02
L13	0	12 and ((anti near3 diffusion) ((anti near5 punch near5 through)anti-punchthrough APT))	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/09 19:02
S1	2530903	well	US-PGPUB; USPAT	OR	ON	2004/08/03 15:19
S2	486563	well and oxide	US-PGPUB; USPAT	OR	ON	2004/08/03 15:20
S3	111207	(well and oxide) and (implant\$3 dop\$4)	US-PGPUB; USPAT	OR	ON	2004/08/03 15:21
S4	91546	((well and oxide) and (implant\$3 dop\$4)) and (trench open\$3 via hole recess groove)	US-PGPUB; USPAT	OR	ON	2004/08/03 15:22

S5	66906	((well and oxide) and (implant\$3 dop\$4)) and (trench open\$3 via hole recess groove) and (etch\$3 pattern\$4)	US-PGPUB; USPAT	OR	ON	2004/08/03 15:23
S6	25847	(((well and oxide) and (implant\$3 dop\$4)) and (trench open\$3 via hole recess groove) and (etch\$3 pattern\$4)) and ((tunnel gate) near5 (oxide dielectric))	US-PGPUB; USPAT	OR	ON	2004/08/03 15:25
S7	25552	((((well and oxide) and (implant\$3 dop\$4)) and (trench open\$3 via hole recess groove) and (etch\$3 pattern\$4)) and ((tunnel gate) near5 (oxide dielectric))) and (silicon polysilicon (poly near3 crystal\$6 near3 silicon))	US-PGPUB; USPAT	OR	ON	2004/08/03 15:28
S8	7355	((((((well and oxide) and (implant\$3 dop\$4)) and (trench open\$3 via hole recess groove) and (etch\$3 pattern\$4)) and ((tunnel gate) near5 (oxide dielectric))) and (silicon polysilicon (poly near3 crystal\$6 near3 silicon))) and (isolat\$3 near5 trench))	US-PGPUB; USPAT	OR	ON	2004/08/03 15:28
S9	1142	(((((((well and oxide) and (implant\$3 dop\$4)) and (trench open\$3 via hole recess groove) and (etch\$3 pattern\$4)) and ((tunnel gate) near5 (oxide dielectric))) and (silicon polysilicon (poly near3 crystal\$6 near3 silicon))) and (isolat\$3 near5 trench)) and (pad near5 nitride))	US-PGPUB; USPAT	OR	ON	2004/08/03 15:30
S10	1156	(((((((well and oxide) and (implant\$3 dop\$4)) and (trench open\$3 via hole recess groove) and (etch\$3 pattern\$4)) and ((tunnel gate) near5 (oxide dielectric))) and (silicon polysilicon (poly near3 crystal\$6 near3 silicon))) and (isolat\$3 near5 trench)) and (pad near5 nitride))	US-PGPUB; USPAT	OR	ON	2004/08/24 14:41
S11	3	(((((((well and oxide) and (implant\$3 dop\$4)) and (trench open\$3 via hole recess groove) and (etch\$3 pattern\$4)) and ((tunnel gate) near5 (oxide dielectric))) and (silicon polysilicon (poly near3 crystal\$6 near3 silicon))) and (isolat\$3 near5 trench)) and (pad near5 nitride)) and (anti near5 (diffusion puch))	US-PGPUB; USPAT	OR	ON	2004/08/24 12:07

S12	568	(((((well and oxide) and (implant\$3 dop\$4)) and (trench open\$3 via hole recess groove)) and (etch\$3 pattern\$4)) and ((tunnel gate) near5 (oxide dielectric))) and (silicon polysilicon (poly near3 crystal\$6 near3 silicon))) and (isolat\$3 near5 trench)) and (pad near5 nitride)) and (threshold near5 volt\$3)	US-PGPUB; USPAT	OR	ON	2004/08/24 12:47
S13	439	(((((well and oxide) and (implant\$3 dop\$4)) and (trench open\$3 via hole recess groove)) and (etch\$3 pattern\$4)) and ((tunnel gate) near5 (oxide dielectric))) and (silicon polysilicon (poly near3 crystal\$6 near3 silicon))) and (isolat\$3 near5 trench)) and (pad near5 nitride)) and (threshold near5 volt\$3)) and depth	US-PGPUB; USPAT	OR	ON	2004/08/24 12:38
S14	2578	triple near5 well	US-PGPUB; USPAT	OR	ON	2004/08/24 14:42
S15	2100	(triple near5 well) and (trench open\$3 via hole recess groove)	US-PGPUB; USPAT	OR	ON	2004/08/24 14:43
S16	950	((triple near5 well) and (trench open\$3 via hole recess groove)) and (threshold near5 volt\$6)	US-PGPUB; USPAT	OR	ON	2005/01/09 18:30
S17	20946	DHF BOE	US-PGPUB; USPAT	OR	ON	2005/01/09 18:31
S18	15548	(DHF BOE) and (trench open\$3 via hole recess groove)	US-PGPUB; USPAT	OR	ON	2004/08/24 12:47
S19	600	((DHF BOE) and (trench open\$3 via hole recess groove)) and (threshold near5 volt\$6)	US-PGPUB; USPAT	OR	ON	2004/08/24 12:49
S20	7	(((((well and oxide) and (implant\$3 dop\$4)) and (trench open\$3 via hole recess groove)) and (etch\$3 pattern\$4)) and ((tunnel gate) near5 (oxide dielectric))) and (silicon polysilicon (poly near3 crystal\$6 near3 silicon))) and (isolat\$3 near5 trench)) and (pad near5 nitride)	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/24 14:41
S21	321	triple near5 well	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/24 14:43
S22	47	(triple near5 well) and (trench open\$3 via hole recess groove)	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/24 14:43